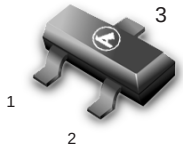
# Dual Serise Switching Diodes

**LDAN202UT1**



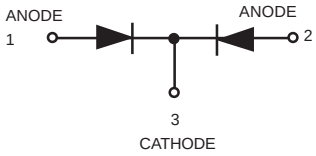

**SOT-323/SC-70**

### FEATURES

- Ultra high speed switching
- Suitable for high packing density layout.
- High reliability.
- Pb-Free package is available.

### DEVICE MARKING AND ORDERING INFORMATION

| Device | Marking | Shipping |
|---|---|---|
| LDAN202UT1 | N | 3000/Tape&Reel |
| LDAN202UT1G (Pb-Free) | N | 3000/Tape&Reel |




### MAXIMUM RATINGS (Each Diode)

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Reverse Voltag | $V_R$ | 80 | Vdc |
| Forward Current | $I_o$ | 100 | mAdc |
| Peak Forward Surge Current | $I_{FM(surge)}$ | 300 | mAdc |
| Forward voltage(If = 100mA ) | $V_F$ | 1.2 | V |
| Reverse current (Vr = 70V ) | $I_R$ | 0.1 | uA |
| Capacitance between terminals(f =1MHz) | $C_T$ | 3.5 | pF |
| Reverse recovery time(Vr= 6V,If=5 mA) | Trr | 4 | nS |

### ELECTRICAL CHARACTERISTIC CURVES

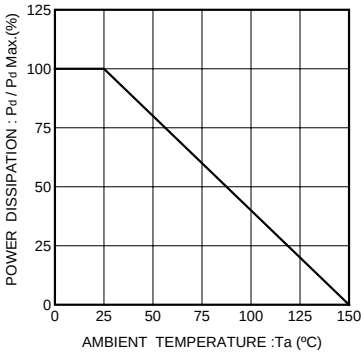



Fig.1 Power attenuation curve

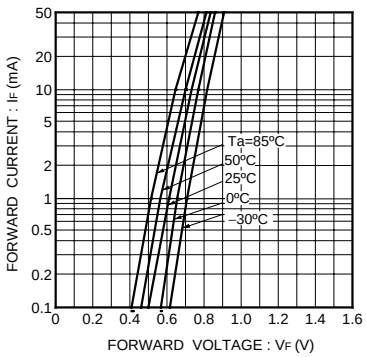



Fig.2 Forward characteristics (P Type)

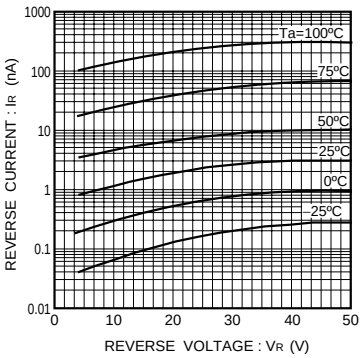



Fig.3 Reverse characteristics (P Type)

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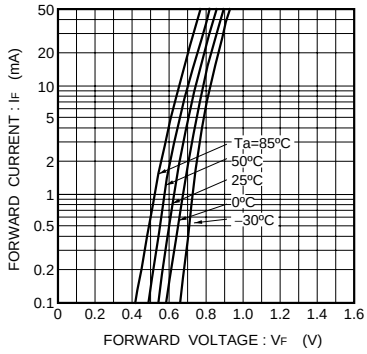


Fig.4 Forward characteristics (N Type)

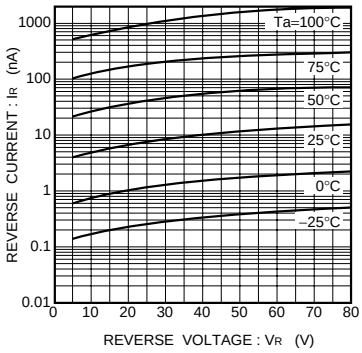


Fig.5 Reverse characteristics (N Type)

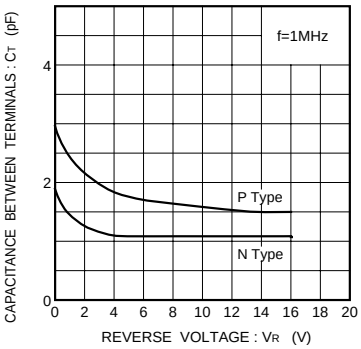


Fig.6 Capacitance between terminals characteristics

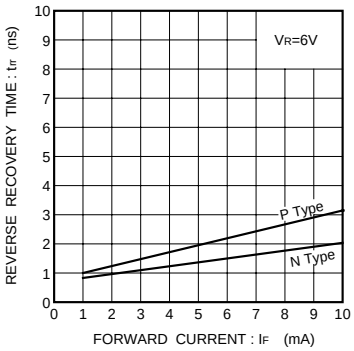


Fig.7 Reverse recovery time

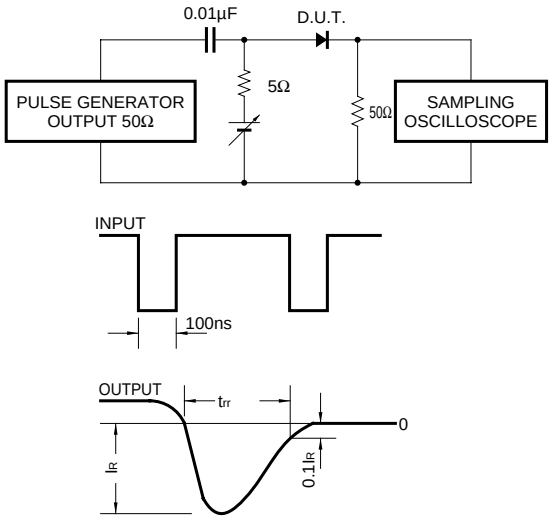


Fig.8 Reverse recovery time ($t_{rr}$) measurement circuit

**LDAN202UT1**

## SC–70 / SOT–323

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| | MIN | MAX | MIN | MAX |
| A | 0.071 | 0.087 | 1.80 | 2.20 |
| B | 0.045 | 0.053 | 1.15 | 1.35 |
| C | 0.032 | 0.040 | 0.80 | 1.00 |
| D | 0.012 | 0.016 | 0.30 | 0.40 |
| G | 0.047 | 0.055 | 1.20 | 1.40 |
| H | 0.000 | 0.004 | 0.00 | 0.10 |
| J | 0.004 | 0.010 | 0.10 | 0.25 |
| K | 0.017 REF | | 0.425 REF | |
| L | 0.026 BSC | | 0.650 BSC | |
| N | 0.028 REF | | 0.700 REF | |
| S | 0.079 | 0.095 | 2.00 | 2.40 |